Small Signal MOSFET –100V, 18Ω, –170mA, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- High Voltage (100V)
- 4V drive
- High Speed Switching and Low Loss
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

• Lithium-ion Battery Charging and Discharging Cell Balance

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-100	V
Gate to Source Voltage	VGSS	±20	V
Drain Current (DC)	ID	-170	mA
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	-680	mA
Power Dissipation When mounted on ceramic substrate (900mm ² \times 0.8mm)	PD	0.6	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit	
Junction to Ambient When mounted on ceramic substrate ($900mm^2 \times 0.8mm$)	R _{θJA}	208	°C/W	

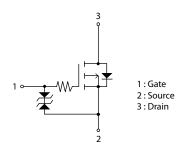


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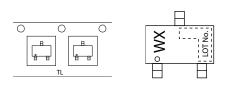
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VDSS	R _{DS} (on) Max	ID Max
-100V	18Ω@ –10V	470
	21Ω@ –4V	–170mA

ELECTRICAL CONNECTION P-Channel



PACKING TYPE : TL MARKING



ORDERING INFORMATION

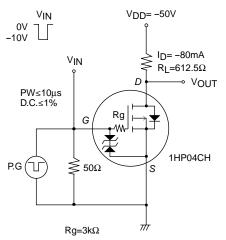
See detailed ordering and shipping information on page 5 of this data sheet.

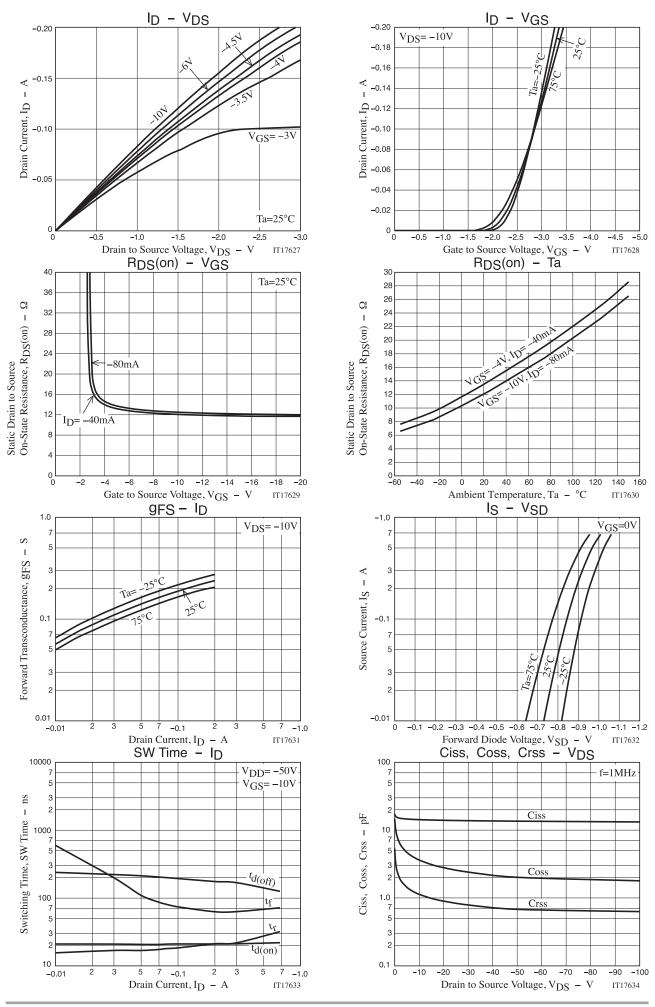
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

Devenueter	C: mah al	Conditions	Value			1.1
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-100			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-100V, V _{GS} =0V			-1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±16V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =–10V, I _D =–100μA	-1.2		-2.6	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-80mA		170		mS
Static Drain to Source On-State	R _{DS} (on)1	ID=-80mA, VGS=-10V		12.5	18	Ω
Resistance	R _{DS} (on)2	ID=-40mA, VGS=-4V		14	21	Ω
Input Capacitance	Ciss			14		pF
Output Capacitance	Coss	V _{DS} =–20V, f=1MHz		2.8		pF
Reverse Transfer Capacitance	Crss			0.9		pF
Turn-ON Delay Time	t _d (on)			21		ns
Rise Time	tr			18		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		200		ns
Fall Time	tf			81		ns
Total Gate Charge	Qg			0.9		nC
Gate to Source Charge	Qgs	V _{DS} =-50V, V _{GS} =-10V, I _D =-170mA		0.14		nC
Gate to Drain "Miller" Charge	Qgd			0.27		nC
Forward Diode Voltage	V _{SD}	IS=-170mA, VGS=0V		-0.88	-1.2	V

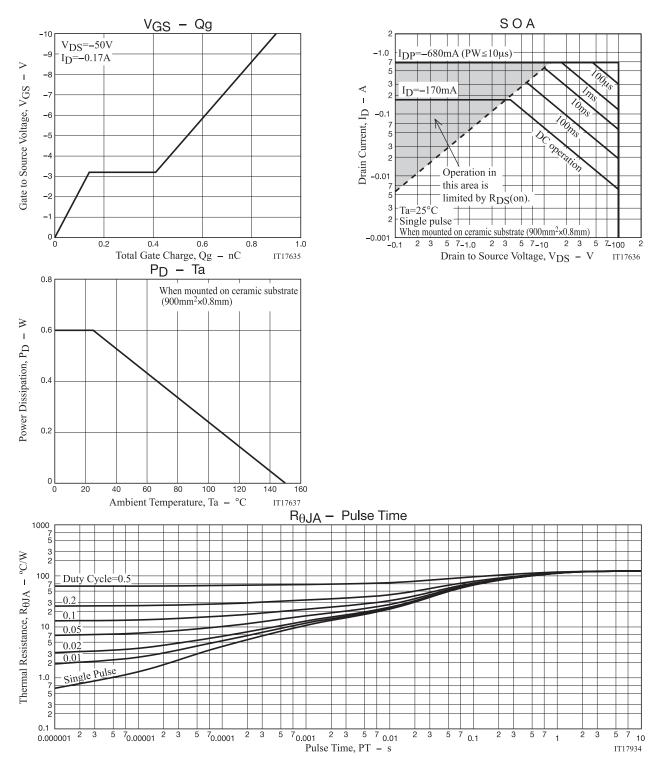
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





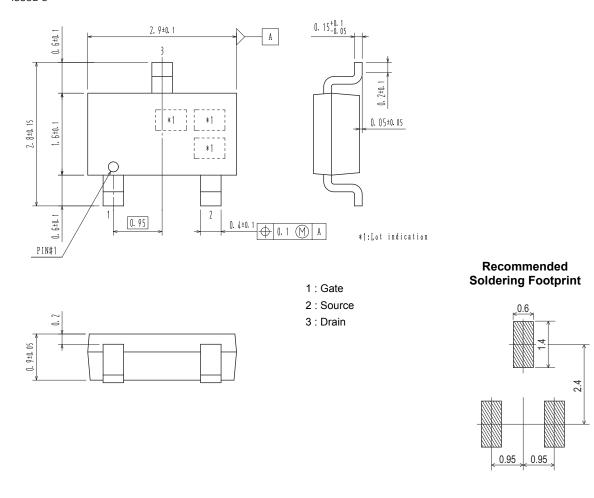
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PACKAGE DIMENSIONS

unit : mm

CPH3 CASE 318BA ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
1HP04CH-TL-W	WX	CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	3,000 / Tape & Reel	

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the 1HP04CH is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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